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(Not for submission under 37 CFR 1.99)

Application Number	10596726
Filing Date	2006-06-22
First Named Inventor	Dan YANSON
Art Unit	2813
Examiner Name	Vicki B. BOOKER
Attorney Docket Number	35832.000130

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1	YI, H.T. ET AL. "Effect of dielectric and semiconductor cap layer combinations in impurity free vacancy disordering of an InGaAs/InGaAsP single quantum well structure", Sae Mulli. Vol. 41, pp.193-8 (Sept. 2000)	<input type="checkbox"/>
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